

## Research Article

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# Accelerated materials design approaches based on structural classification: application to low enthalpy high pressure phases of $\text{SH}_3$ and $\text{SeH}_3$

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**Abstract:** We propose a methodology that efficiently assesses major characteristics in the energy landscape for a given space of configurations (crystal structures) under pressure. In this work we study  $\text{SH}_3$  and  $\text{SeH}_3$ , both of fundamental interest due to their superconducting properties. Starting from the crystal fingerprint, which defines configurational distances between crystalline structures, we introduce an optimal one dimensional metric space that is used to both classify and characterize the structures. Furthermore, this is correlated to the electronic structure. Our analysis highlights the uniqueness of the  $Im - 3m$  phase of  $\text{H}_3\text{S}$  and  $\text{H}_3\text{Se}$  for superconductivity. This approach is an useful tool for future material design applications.

The theoretical prediction by Duan et al. [1] and the successful experimental discovery by Drozdov et al. [2] of superconductivity in  $\text{H}_3\text{S}$  at 200 GPa, with the record critical temperature ( $T_C$ ) of 203 K, rekindled the century-old dream of a room temperature superconductor. A plethora of hydrogen rich materials have been proposed in the quest for novel high- $T_C$  superconductors, as the presence of hydrogen seems to be fundamental to reach the very high phonon frequencies, strong electron-phonon coupling, and therefore high critical temperatures [3–6]. A major emphasis has been given to the class of hydrides [7–19] such as silane [8, 20–23], disilane [24], sulfur hydride [25–33], sodium hydride [34], to name a few.

It is clear that in this research field a key role is played by materials design algorithms [35, 36] both providing predictions [1, 37, 38], prior to experiments, and helping with their interpretation afterwards [39–44]. Several of these computational synthesis tools exist: evolutionary

based algorithms [45], particle swarm optimization [46], random sampling methods [47], and hopping based algorithms [48], to name a few.

What all these tools have in common is the use density functional theory (DFT) as the workhorse to evaluate energy and forces due to its reasonable accuracy for a relatively moderate computational cost and overall reproducibility [49]. Within the global optimization codes, what the routines usually do is to rank structures according to their total energy. One usually expects that the absolute enthalpy minimum is the one experimentally realized and many significant predictions have been made in this way. However, due to the limited intrinsic precision of DFT functionals, to the accuracy limit of the computational methods, as well as the non ideal experimental conditions (for instance under high pressure non hydrostaticity can play an important role in the synthesis), all the low enthalpy structures may be experimentally relevant as in the case discussed in Ref. [39].

In this work we consider hydrogen sulfide and hydrogen selenide systems, also studied in Ref. [37], as test case to present a method for the characterization of structures based on fingerprint classification of energetically competitive structures, i.e. in the vicinity of the global minimum structure. We will focus on some key aspects of this classification, in particular on the problem of structural similarity, and the relation with electronic properties. Besides the possible experimental relevance of the set of these low enthalpy structures, as mentioned before, this approach is also useful post-analysis to help in the characterization of the configurational energy landscape for finite systems, and could be used to improve crystal prediction algorithms.

We start from the calculation of the energetically competitive structures in  $\text{H}_3\text{S}$  and  $\text{H}_3\text{Se}$  at high pressure found by the crystal prediction minima hopping method [48] at the level of DFT (sec. 1). We then analyze the predicted structures by means of the structural fingerprint method as introduced by Zhu *et al* [50, 51] (sec. 2). Based on this structural fingerprint, we define an optimal one dimen-

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sional classification (sec. 3.1) that further is correlated to a more general trend, the electronic density of states (DOS).

## 1 Computational Details

Structural data was generated by using *ab initio* crystal structure prediction, minima hopping method (MHM) [52]. Given only the chemical composition of a system, the MHM aims at finding the global minimum on the enthalpy surface while gradually exploring low-lying structures. This method has been successfully used for global geometry optimization in a large variety of applications [53–57]. Previously we have explored selenium and sulfur hydride under pressure with MHM [37]. We have restricted the study to considered only simulations cells with single formula unit of Se and S -H<sub>3</sub> at different pressures between 50 and 200 GPa. Once identified the global minimum, we allow the algorithm to visit even higher energy structures up to 2 eV. Hundred's of visited structures were relaxed with tight convergence at the density-functional theory level using the Perdew-Burke-Ernzerhof exchange-correlation function [58] and plane-wave basis set with of 900 eV was used to expand the wave function together with the projector augmented wave (PAW) method as implemented in the Vienna *ab initio* simulation package VASP [59]. Monkhorst-Pack grid meshes with spacing of  $2\pi \times 0.15 \text{ \AA}$  were used, resulting in total energy convergence to better than 2 meV/atom and forces on the atoms were less than 2 meV/Å and the resulting stress less than 1 kB.

## 2 The Crystal Fingerprint method

In order to characterize a crystal structure in condensed matter physics it is most convenient to adopt a Bravais matrix and base representation, that allows for a clear description of symmetry properties and therefore is optimal for computational purposes. However, while this description is excellent to characterize a single system, the description becomes inefficient when comparing hundreds of different crystals closely related, simply because comparisons are not straightforward due to the non-unique representation; the same crystal may be described with an infinite number of different, but equivalent ways. This is the typical situation when working with structures generated by crystal structure prediction methods. One therefore has to introduce alternative descriptions that allow to compare structures on an unambiguous ground. The initial aim of the crystal fingerprints was to solve a very

specific problem, to classify and remove duplicate crystal structures from the results generated by crystal prediction methods. Early work by Oganov-Valle in fingerprints were developed based on local atom distances and analyzed in diffraction spectra type plots [60]. Another interesting approach to this problem was proposed by Ceriotti et al. [61], in which they analyzed the pairwise distribution distances between frames (molecules) and reduced the high dimensional free-energy surface to a sketch map, see for instance Ref. [62]. Another successful crystal representation inspired by radial distribution functions as used in the physics of X-ray powder diffraction, was introduced by Glawe et al. [63] and used for machine learning algorithms. In this work we will use the *configurational fingerprint approach*, and correlate it to the electronic structure of high temperature superconducting materials, thus we briefly review in this section [50, 51].

For each atom  $k$  in a crystal located at  $\mathbf{R}_k$ , we obtain a cluster of atoms by considering only those contained in a sphere centered at  $\mathbf{R}_k$ . For this cluster, one calculates the overlap matrix elements  $S_{i,j}^k$  as described in Ref. [51] for a non-periodic system, i.e., we construct on each atom one or several Gaussian type orbitals and calculate the resulting overlap integral. The orbitals are indexed by the letters  $i$  and  $j$  and the index  $w(i)$  gives the index of the atom on which the Gaussian  $G_i(\mathbf{r})$  is centered, i.e.,

$$S_{i,j}^k = \int d\mathbf{r} G_i(\mathbf{r} - \mathbf{R}_{w(i)}) G_j(\mathbf{r} - \mathbf{R}_{w(j)}) \quad (1)$$

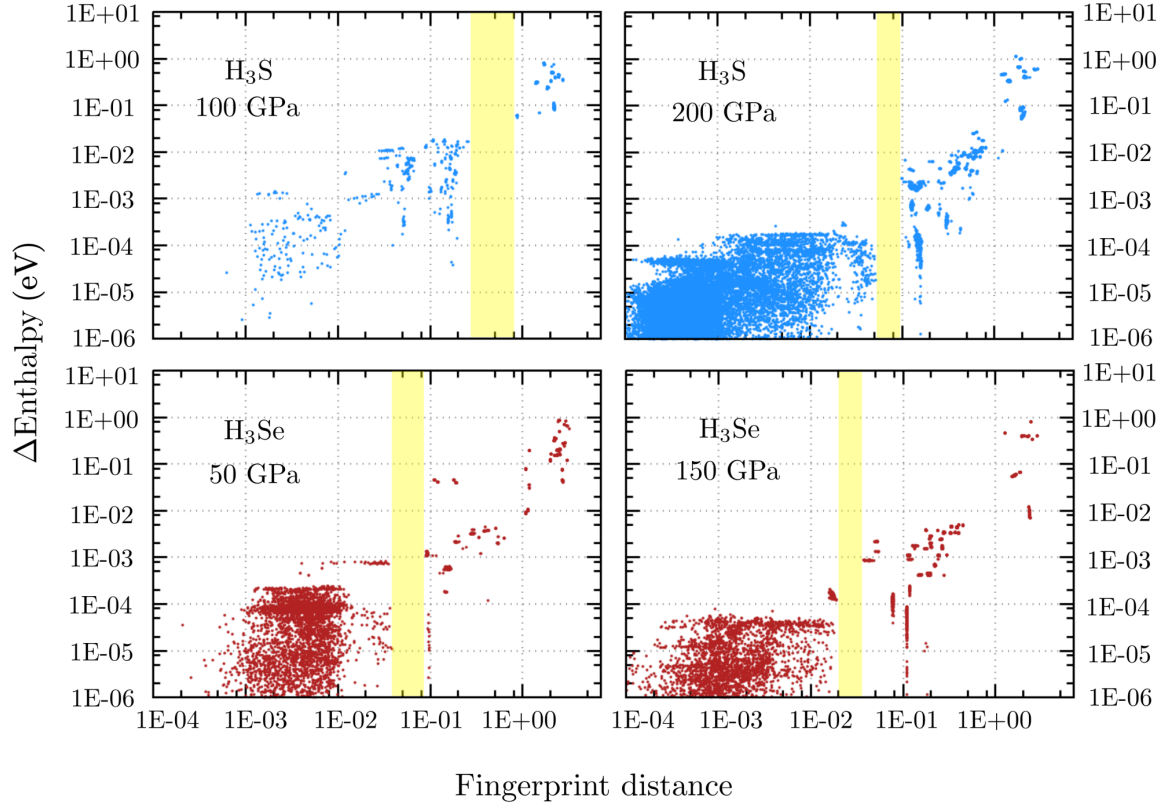
In this first step, the amplitudes of the Gaussians  $c_{\text{norm}}$  are chosen such that the Gaussians are normalized to one, and the width of each Gaussian  $G_i(\mathbf{r})$  is given by the covalent radius of the atom  $w(i)$  on which it is centered. To avoid discontinuities in the eigenvalues when an atom enters into or leaves the sphere, a second step constructs a matrix  $T^k$  such that

$$T_{i,j}^k = f_c(|\mathbf{R}_{w(i)} - \mathbf{R}_k|) S_{i,j}^k f_c(|\mathbf{R}_{w(j)} - \mathbf{R}_k|). \quad (2)$$

The cutoff function  $f_c$  smoothly goes to zero on the surface of the sphere with radius  $\sqrt{2n\sigma_c}$ ,

$$f_c = \left( 1 - \frac{r^2}{2n\sigma_c^2} \right)^n. \quad (3)$$

In the limit where  $n$  tends to infinity, the cutoff function converges to a Gaussian of width  $\sigma_c$ . This characteristic length scale is typically chosen to be the sum of the two largest covalent radii in the system. The value  $n$  determines how many derivatives of the cutoff function are continuous on the surface of the sphere (in our case  $n = 3$  was used). One can consider the modified matrix  $T^k$  to be the overlap matrix of the cluster where the amplitude of



**Figure 1:** (Top panels) show the correlation between the enthalpy difference (eV/unit cell) and the fingerprint distance (arbitrary units) for  $\text{H}_3\text{S}$  at 100 GPa and 200 GPa and (Bottom panels) for  $\text{H}_3\text{Se}$  at 50 GPa and 150 GPa. Each point in the plot correlates energy difference and fingerprint distance between two structures. For each set of structures, the enthalpy difference is with respect to the global minimum. Based on energetics, different structures are distinguishable above 10 meV (1E-02 eV/u.c.); below this threshold the structures are considered identical. Indicated in yellow areas is the fingerprint "gap", in which the function differentiates between structures.

the Gaussian at atom  $i$  is determined by  $c_{\text{norm}} f_c(|\mathbf{R}_i - \mathbf{R}_k|)$ . In this way atoms close to the surface of the sphere give rise to very small eigenvalues of  $T^k$  and are weighted less than the atoms closer to the center.

The eigenvalues of this matrix  $T^k$  are sorted in descending order and form the atomic fingerprint vector  $\mathbf{V}_k$ .<sup>1</sup> The Euclidean norm  $|\mathbf{V}_k - \mathbf{V}_l|$  measures the dissimilarity between the atomic environments of atoms  $k$  and  $l$ .

<sup>1</sup> Since one cannot predict exactly how many atoms will be in the sphere, we estimate a maximum length for the atomic fingerprint vector. If the number of atoms is too small to generate enough eigenvalues to fill up the entire vector, the entries at the end of the fingerprint vector are filled up with zeros. This also guarantees that the fingerprint is a continuous function with respect to the motion of the atoms when atoms might enter or leave the sphere. If an atom enters into the sphere, some zeros towards the end of the fingerprint vector are transformed in a continuous way into some very small entries which only contribute little to the overall fingerprint.

The atomic fingerprints  $\mathbf{V}_k^p$  and  $\mathbf{V}_k^q$  of all the  $N_{\text{at}}$  atoms in two crystalline configurations  $p$  and  $q$  can now be used to define a *fingerprint distance* (FD)  $d(p, q)$  between two crystals,

$$d(p, q) = \min_P \left( \sum_k^{N_{\text{at}}} |\mathbf{V}_k^p - \mathbf{V}_{P(k)}^q|^2 \right)^{1/2} \quad (4)$$

where  $P$  is a permutation function which matches a certain atom  $k$  in crystal  $p$  with atom  $P(k)$  in crystal  $q$ . The optimal permutation function which minimizes  $d(p, q)$  can be found with the Hungarian algorithm [64] in polynomial time. If the two crystals  $p$  and  $q$  are identical, the Hungarian algorithm will in this way assign corresponding atoms to each other. The Hungarian algorithm needs as its input only the cost matrix  $C$  given by

$$C_{k,l} = |\mathbf{V}_k^p - \mathbf{V}_l^q|^2. \quad (5)$$

A key concept is that  $d(p, q)$  satisfies the properties of a metric, positiveness, symmetry, coincidence axiom and

the triangle inequality, and have been demonstrated in the work by Zhu *et al.*[50]. We restrict this study only to the use of  $\mathbf{R}_k$  typical s-type Gaussian orbitals with centered spheres (with about 80-120 atoms).

### 3 Results

In Fig 1 we plot the FD versus enthalpy difference. For the low pressure case of  $\text{H}_3\text{S}$  we consider 63 structures, for the high pressure (200 GPa) 423 structures.  $\text{H}_3\text{Se}$  contains 227 for the low pressure and 241 structures for the high pressure. Each point in these plot correlates energy difference and fingerprint distance between two structures. For each set of pressure, the energy difference is with respect the global minimum. An ideal fingerprint produces, in these type of plots, a clear gap along the FD axis, clearly separating structures that are classified as identical from those that are different. In both materials, independently of pressure there is a clear distinguishable gap. After visual inspection of the structures, we observe that many of the structures are fairly similar and hardly distinguishable by eye, many of them only having small distortions of hydrogen and different vector cell description. Based on energetics, and after visual inspection, different structures are distinguishable above 10 meV (1E-02 eV/u.c.), below this threshold the structure is consider identical. Fingerprint distances (FD)  $> 0.1$  can differentiate between structures for the case of  $\text{SH}_3$  at low pressure. We confirm that at low pressure, both systems still have high molecular nature, this also means that many energetically degenerated structures are possible withing little change in their energies (we will come back to this point in the next section). However, at high pressure the situation changes and in both systems the fingerprint distance is shifted toward lower FD values. For instance in  $\text{H}_3\text{S}$  at 200 GPa FD is 4E-02, while for selenium-hydride we found the gap for  $> 2\text{E}-02$  FD values. We found that there is a clear correlation in both systems between pressure and fingerprint distance, i.e. the gap is shifted towards lower FD values as increasing pressure. This is due to the changes in the potential energy landscape; as increasing pressure in both systems there are much less structures with small variations in the hydrogen positions.

#### 3.1 Optimal 1D classification of crystal structures

As seen in Sec. 2, the structural fingerprint maps the structures into a metric space. This allows for further analysis but still lacks the possibility for a simple (visual) representation since this space still is a high dimensional one. For a simply representation it would be best to map it into an Euclidean space of low dimensionality (degree two or three). This means to associate, to each element in the set (crystal), coordinates in an Euclidean space in such a way that the distance is as close as possible to the fingerprint distance. Clearly the higher the dimension, the more accurate would be the mapping, however at the cost of being less intuitive the graphical representation.

Since the case of the (low enthalpy)  $\text{SH}_3 / \text{SeH}_3$  structures is relatively simple (and we known the global minimum), we can consider for this work the case of a one dimensional representation, for that we introduce a rather simple mapping algorithm and yet easily expandable to higher dimensions: we associate to each crystal in the set a random position in the one dimensional space, such a way the length scale of the distribution is of the order of the average fingerprint distance. Then we define the following force field:

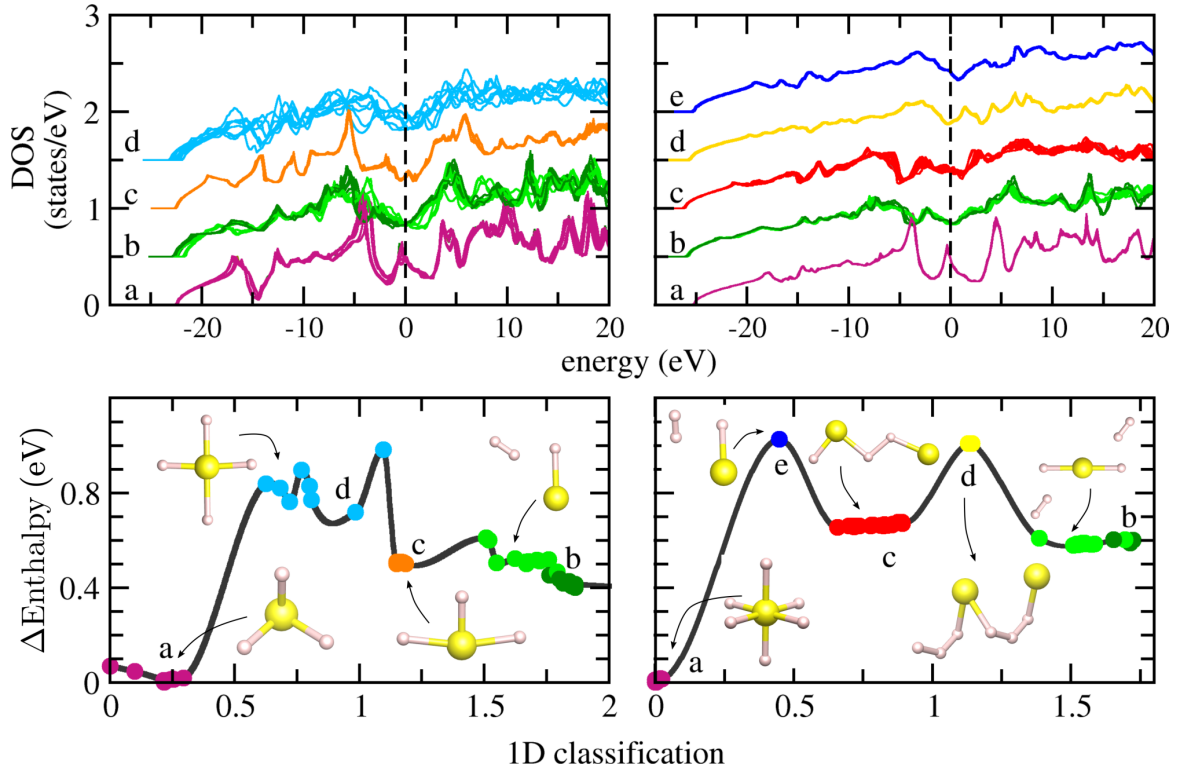
$$F(i, j) = \text{sgn}(x_i - x_j) |(x_i - x_j) - d(i, j)| \quad (6)$$

for all pairs of systems  $i$ , and  $j$ , where  $x_i$  and  $x_j$  are the position in the 1D axis. And we run dynamics. Since many local minima exist, the operation is repeated for different starting order (randomized) to minimize the quantity

$$S = \sum_{i,j} |(x_i - x_j) - d(i, j)|. \quad (7)$$

This stochastic approach may require many iterations to reach the optimal configuration especially in multidimensional spaces and when large number of systems are involved. In the systems considered in this work and for the number of structures, the algorithm finds a minimum within a few thousand iterations (a couple of minutes of computing time). Other alternative to use instead, while dealing for larger data-sets, is to resort genetic algorithms. This have been proved to efficiently solve similar mathematical problems, as in Ref. [65].

The resulting 1D optimization is shown in the bottom panels of Fig. 2 and Fig. 3, respectively for  $\text{SH}_3$  and  $\text{SeH}_3$ . First we can distinguish that structures are more clustered at high pressure than at low pressure, this indicates that at high pressure the crystal data-set covers all the well defined minima, while at lower pressure a larger number

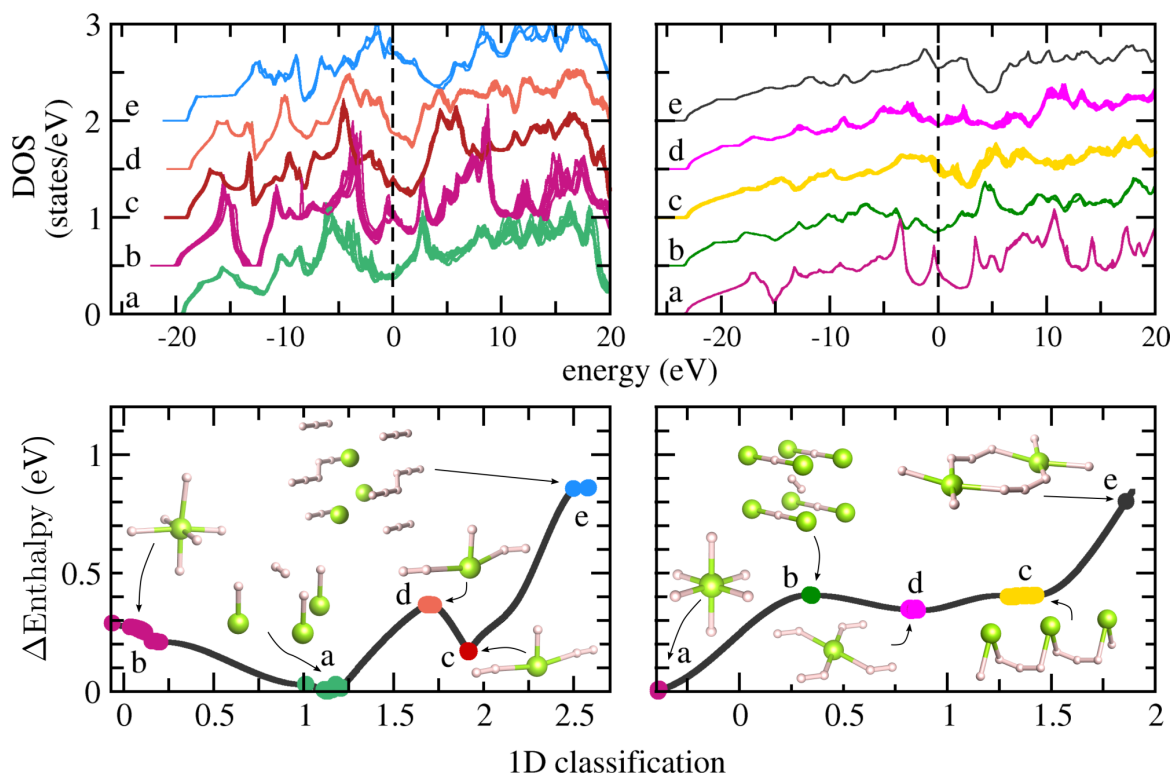


**Figure 2:** (Color online) Density of states (top panels) and one dimensional classification (bottom –see text) of  $\text{SH}_3$  structures generated by the minima hopping algorithm, at 100 GPa of pressure (left) and at 200 GPa of pressure (right). The color code is used to match a structure group with its corresponding density of states (and alphabetically labeled). The solid black lines that connect the points (bottom panels) serve only as guide to the eye. In the structures, hydrogen is represented in white and sulfur in yellow. For each family we shown a representative structure for the data set, depicting variations in structure motif, coordination number and bond type.

of different structures are found. These can be local minima but also saddle points, since the only criterion for their convergence is a threshold on the inter-atomic forces. Note also that all the structures (including the lowest energy one) could be unstable towards phonon displacement with finite  $\mathbf{q}$ . The full dynamic stability has to always be verified (independently) to guarantee that a given prediction is physically relevant. At lower pressures (particularly evident for  $\text{SH}_3$  at 100 GPa) we observe a large spread of structures that are distributed in a more homogeneous way on the 1D axis. This indicates that minima in the potential energy surface are very shallow, indeed of a highly molecular nature. We can also see that whenever the structure contains internal blocks of detached  $\text{H}_2$  molecules, the more the FD, and consequently the 1D classification, is spread out, regardless of their energetics, see for example set b and c for  $\text{SH}_3$  at 200 GPa.

One of the most interesting features that result from this type of analysis is the identification of low-enthalpy structures, only 1D distance separated from the global minimum. In short this points to the existence of energet-

ically plausible structures that are structure-wise very different from the ground state and therefore could in principle be accessible to synthesis because they belong to a different funnel. A funnel is the basin of attraction where the global minimum or local minima lives, different funnels are typically separated by high energy barriers and feature distinct structures. However, there are no flagrant cases that point to this situation in these systems, apart from the structure group of  $\text{SeH}_3$  at 50 GPa labeled c and b (see different motifs and similar energetics). Structure b is the pre-cubic structure ( $Im-3m$ ) that becomes stable at high pressure and is superconducting. Although the 1D structure distance from c to b is not large, they are separated enough to be classified as two different funnels, and under further compression both, will evolve to the cubic structure (main attractor funnel at high pressure). We can also point out that the highly metallic cubic structure is always localized by the classification at the (left) edge of the set (violet circles in all classification plots) and in all cases is well separated from the rest of the structures, indicat-



**Figure 3:** (Color online) Density of states (top panels) and one dimensional classification (bottom –see text) of  $\text{SeH}_3$  structures generated by the minima hopping algorithm. At 50 GPa of pressure (left) and at 150 GPa of pressure (right). The color code is use to match a structure group with their corresponding density of states (as well alphabetically labeled). The solid black line that connects the points (bottom panels) serves only as guide to the eye. Hydrogen is represented in white and selenium in green spheres. For each family we shown a representative structure for the data-set, depicting variation in structure motif, coordination number and bond type.

ing the uniqueness of the  $Im - 3m$  phase, in both  $\text{SH}_3$  and  $\text{SeH}_3$  at high pressure.

### 3.2 Correlation between classification and electronic properties

The structure fingerprint distance and the one dimensional classification can be correlated to a more general trend: the electronic density of states (DOS). For this analysis we proceed in the following way: we compute the electronic DOS for all the systems in the sets and group them in classes according to the similarity. This classification can be somehow arbitrary and there are cases (structures) in which it is not uniquely define. For that cases we compute the occupation at the Fermi level (per structure) and build an histogram type plot. As shown in the top panels of Fig. 2 and Fig. 3 a clear separation in families is achieved for all the cases. The Fermi level is set to 0 eV in all the plots. Families are depicted within different colors and correspond to the crystals depicted in the bottom panels.

The 1D classification correctly clustered structures that are labeled as similar and that have similar DOS, after deep investigation we did not find situations in which different classes (families of structures or DOS) overlap. This means that despite of its simplicity, by mapping into the 1D Euclidean space we are able to classify different existent funnels in both compositions. It is also important to notice that spread (structures avoid clustering, as in the low pressure case) in the 1D classification corresponds as well a spread in the shape of the DOS function. This becomes clear and perhaps considered as obvious, but it is not trivial; we are not directly comparing the DOS with the crystal structure, we are stepping through several non trivial steps as the conversion of crystal representation into distances and reducing it to 1D-mapping. Therefore, our mapping is actually allowing a direct comparison between structures and electronic properties without the complexity of the Bravais lattice representation.

From a physical point of view there are some patterns that is worth to point out. The superconducting phase (cubic/rhombohedral)  $Im - 3m/R3m$  respectively at high and

low pressure - see Ref. [37] for details) has always a characteristic sharp peak near the Fermi level, highly metallic in comparison with the rest of structures living in other funnels, that instead tend to show a dip at the Fermi level as in indication of a remaining molecular character in their bonding. This mirrors the fact that the classification locates cubic/rhombohedral phases at the extreme side (in this case left) of the configurational space.

## 4 Conclusions

In this work we presented a new type of analysis and classification for materials design algorithms and we applied it for the first time to the case of high temperature, high pressure, superconducting families  $\text{SH}_3$  and  $\text{SeH}_3$ . Materials design algorithms are intended to compute low enthalpy structures of a system at a given chemical composition. However due to both the limited accuracy of calculations and the complexity of the physical conditions it is not always the case that the experimentally synthesized system has the lowest predicted enthalpy. It is important to develop methods to characterize the full set of predicted structures. Based on the structural fingerprint, we define a metric distance between two given structures. The distances between structures are minimized with a simple algorithm; by doing this we are able to reduce the free-energy landscape to 1D-dimensional representation. With this 1D-dimensional structural classification it is easy to observe patterns of clustering of stable/metastable structures and their grouping into families. We showed that the corresponding structural grouping also corresponds to that of their electronic structure. From this description it appears that the covalent bonded cubic/rhombohedral phase responsible for the measured high  $T_C$  is unique. Finally, our post 1D-dimensional analysis could be useful in genetic-based algorithms for crystal prediction: identifying outsiders at each generation and keeping a good as-set of novelty in crystal motifs, thus accelerating materials design.

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